UFS Lecture 14: Passive Modelocking

7 Mode-Locking using Artificial Fast Sat. Absorbers

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Kerr-lens mode locking: hard aperture versus soft aperture

Hard-aperture Kerr-lens

mode-locking: a hard aperture placed at the right position in the cavity attenuates the wings of the pulse, shortening the pulse.



Soft-aperture Kerr-lens mode-

locking: gain medium can act both as a Kerr medium and as a soft aperture (i.e. increased gain instead of saturable absorption). In the CW case the overlap between the pump beam and laser beam is poor, and the mode intensity is not high enough to utilize all of the available gain. The additional focusing provided by the high intensity pulse improves the overlap, utilizing more of the available gain.



7.1.4 The Kerr Lensing Effect

$$n = n_0 + n_2 I \qquad I(r) = \frac{2P}{\pi w^2} \exp\left[-2(\frac{r}{w})^2\right]$$
$$n(r) = n'_0 \left(1 - \frac{1}{2}\gamma^2 r^2\right), \text{ where}$$
$$n'_0 = n_0 + n_2 \frac{2P}{\pi w^2}, \gamma = \frac{1}{w^2} \sqrt{\frac{8n_2 P}{n'_0 \pi}}.$$

Thin Lens \rightarrow Gaussian Duct

Optical Element	ABCD-Matrix	
Kerr Medium Normal Incidence	$M_{K} = \begin{pmatrix} \cos \gamma t & \frac{1}{n_{0}' \gamma} \sin \gamma t \\ -n_{0}' \gamma \sin \gamma t & \cos \gamma t \end{pmatrix}$	$\gamma_s = \frac{1}{\sqrt{8n_2P}}$
Kerr Medium Sagittal Plane	$M_{Ks} = \begin{pmatrix} \cos \gamma_s t & \frac{1}{n'_0 \gamma_s} \sin \gamma_s t \\ -n'_0 \gamma_s \sin \gamma_s t & \cos \gamma_s t \end{pmatrix}$	$\frac{w_s w_t}{1} \sqrt{\frac{n_0 \pi}{8n_2 P}}$
Kerr Medium Tangential Plane	$M_{Kt} = \begin{pmatrix} \cos \gamma_t t & \frac{1}{n_0^{\prime 3} \gamma_t} \sin \gamma_t t \\ -n_0^{\prime 3} \gamma_t \sin \gamma_t t & \cos \gamma_t t \end{pmatrix}$	$\gamma_t = \frac{1}{w_s w_t} \sqrt{\frac{1}{n_0' \pi}}$

Table 7.2: ABCD matrices for Kerr media

$$\begin{split} \delta_{s,t} &= \frac{1}{p} \frac{w_{s,t}(P,z) - w_{s,t}(P=0,z)}{w_{s,t}(P=0,z)} \\ p &= P/P_{crit}, \text{ with } P_{crit} = \lambda_L^2 / \left(2\pi n_2 n_0^2\right) \end{split}$$

 $R_1 = R_2 = 10$ cm $L_1 = 104$ cm, $L_2 = 86$ cm, t = 2 mm, n = 1.76 and P = 200 kW.





Fig. 7.16: Soft aperture KLM

Evolution of shortest pulse duration



7 Kerr-Lens and Additive Pulse Mode Locking 7.2 Additive Pulse Mode Locking



Fig. 7.17: Principle mechanism of APM



Fig. 7.18: Noninear Mach-Zehnder Interferometer



Figure 7.20: Normalized saturable absorber coefficient $\gamma / \left[\left(\frac{2\pi}{\lambda} \right) \frac{n_2}{A_{eff}} L_{Kerr} l \right]$ as a function of r^2 with loss l as parameter [25].

7.2 Additive pulse mode locking using nonlinear polarization rotation in a fiber



- When an intense optical pulse travels in an isotropic optical fiber, intensitydependent change of the polarization state can happen.
- The polarization state of the pulse peak differs from that of the pulse wings after the fiber section due to Kerr effect.
- If a polarizer is placed after the fiber section and is aligned with the polarization state of the pulse peak, the pulse wings are attenuated more by the polarizer and the pulse becomes shorter.

200 MHz Soliton Er-fiber Laser modelocked by APM



- 167 fs pulses
- 200 pJ intracavity pulse energy
- 200 pJ output pulse energy

K. Tamura et al. Opt. Lett. 18, 1080 (1993).J. Chen et al, Opt. Lett. 32, 1566 (2007).



Fig. 6.1: Principles of mode locking

6.3 Soliton Mode Locking



Saturable Absorption, $q(x) / q_0$



Fig. 6.8: Soliton Stability



Fig. 6.9: Normalized gain, soliton and continuum. The continuum is a long pulse exploiting the peak of the gain.



Fig. 6.10: Measured (---) and simulated (- - -) spectra from a semiconductor saturable absorber modelocked Ti:sapphire laser for different net intracavity dispersion.



Fig. 6.11: Measured (----) and simulated (- - -) autocorrelations corresponding to the spectra shown in Figure 6.11

8 Semiconductor Saturable Absorbers



Fig. 8.1: Band Gap and lattice constant for various compound semiconductors. Dashed lines indicate ind. transitions.



Fig. 8.2: Semiconductor saturable absorber mirror (SESAM) or Semiconductor Bragg mirror (SBR)



Fig. 8.3: Ti:sapphire laser modelocked by SBR

8.1 Carrier dynamics in semiconductors



Table 8.4: Carrier dynamics in semiconductors



Fig. 8.5: Pump probe of a InGaAs multiple QW absorber



Fig. 8.7: GaAs saturable absorber on metal mirror

Satura

d

 T_2

- 0



Fig. 8.6: Saturation fluence and pump probe measured with 10 fs pulses

8.2 High Fluence Effects



Fig. 8.8: Pump probe with low and high fluence



Fig. 8.9: TPA and FCA



Fig. 8.10: Resonantly enhanced SBR



Fig. 8.11: Saturation fluence measurement of resonant absorber

8.3 Break-up into multiple pulses



Fig. 8.12: Difference in loss experienced by a sech-shaped pulse in a slow (- - -) and a fast (_____) saturable absorber for a given pulse energy or peak power, respectively.



Fig. 8.13: Pulse intensity profiles after 20,000 round-trips each. Laser modelocked with sat. abs with recovery time $\tau_A = 200$ fs.



Fig. 8.14: Steady state pulse width and time-bandwidth product



Fig. 8.15: Pulse width of Nd:glas laser.



Fig. 8.16: Pulse intensity profiles after 20,000 round-trips each. Laser modelocked with sat. abs with shorter recovery time $\tau_A = 100$ fs.